

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-5. (Canceled)

6. (Previously presented) A semiconductor substrate device, comprising:

a first semiconductor substrate including a concave-convex surface, the concave-convex surface comprising a convex portion including a top surface; and

a second semiconductor substrate having a thin film oxide insulator on a surface thereof, the surface of the second semiconductor substrate on which the thin film oxide insulator is provided being implanted with hydrogen ions,

wherein the first semiconductor substrate and the second semiconductor substrate are brought together so that the top surface of the convex portion of the concave-convex surface of the first semiconductor substrate and the thin film oxide insulator provided on the ion implanted surface of the second semiconductor substrate contact each other with no circuit or device element located therebetween, to form a two-dimensional array of cavities in the semiconductor substrate device.

7-14. (Canceled)

15. (Previously presented) The device of claim 6, wherein the two-dimensional array of cavities serve as respective low dielectric constant portions so that parasitic capacitance generated between the first substrate and circuit elements on the second substrate is reduced.

16. (Canceled)